

**In the Claims:**

1-45. (Cancelled)

46. (Currently Amended) A method of shaping a surface of a silicon carbide substrate, comprising:

patterning a mask layer on the silicon carbide substrate using a laser to remove material from the mask layer, wherein patterning the mask layer comprises applying laser light to the mask layer at an energy sufficient to remove material from the mask layer while scanning a pattern into the mask layer to form three dimensional geometric patterns in the mask layer; and

etching the silicon carbide substrate using the patterned mask layer to define the three dimensional geometric patterns, wherein the three dimensional geometric patterns comprise a plurality of different geometric patterns.

47. (Original) The method of Claim 46, wherein the mask is a polymer mask.

48. (Original) The method of Claim 46, further comprising forming a light emitting element on the substrate.

49. (Currently Amended) The method of Claim 46, wherein a shape of the ~~pattern~~ three dimensional geometric patterns of the mask layer is based on a difference between an etch rate of the silicon carbide substrate and an etch rate of the mask layer.

50. (Currently Amended) The method of Claim 46, further comprising forming a micro-mask between the mask layer and the silicon carbide substrate, the micro-mask being configured to roughen a surface of the substrate during the etching.

51. (Original) The method of Claim 50, wherein the micro-mask comprises an aluminum layer between the mask layer and the substrate.

52. (Cancelled).

53. (Currently Amended) The method of Claim 46, wherein the plurality of different geometric ~~patters~~-patterns are provided in a single etch and in a single patterning of the mask layer.

54-75. (Cancelled).

76. (New) The method of Claim 53, wherein the plurality of different geometric patterns comprise surfaces that are angled with respect to the surface of the silicon carbide substrate.

77. (New) A method of shaping a surface of a silicon carbide substrate, comprising:

forming a mask layer on the surface of the silicon carbide substrate;

patterning the mask layer using a laser to remove material from the mask layer, wherein patterning the mask layer comprises scanning laser light onto the mask layer at an energy sufficient to remove material from the mask layer to form three-dimensional geometric features in the mask layer having sidewalls that are angled relative to the surface of the substrate; and

anisotropically etching the silicon carbide substrate using the patterned mask layer to define the three dimensional geometric patterns having sidewalls that are angled relative to the surface of the substrate.